Markus Weyers

List of Publications by Citations

495 papers	9,086 citations	41 h-index	74 g-index
536 ext. papers	10,220 ext. citations	2.1 avg, IF	5.76 L-index

#	Paper	IF	Citations
495	Red Shift of Photoluminescence and Absorption in Dilute GaAsN Alloy Layers. *Japanese Journal of Applied Physics*, **1992**, 31, L853-L855	1.4	663
494	Advances in group III-nitride-based deep UV light-emitting diode technology. *Semiconductor Science and Technology*, **2011**, 26, 014036	1.8	525
493	Application of GaN-based ultraviolet-C light emitting diodes--UV LEDs--for water disinfection. *Water Research*, **2011**, 45, 1481-9	12.5	281
492	Recognition and imitation of pantomimed motor acts after unilateral parietal and premotor lesions: a perspective on apraxia. *Neuropsychologia*, **2001**, 39, 200-16	3.2	182
491	Growth of GaAsN alloys by low-pressure metalorganic chemical vapor deposition using plasma-cracked NH3. *Applied Physics Letters*, **1993**, 62, 1396-1398	3.4	178
490	A comparative study of Ga(CH3)3 and Ga(C2H5)3 in the mombe of GaAs. *Journal of Crystal Growth*, **1986**, 74, 292-300	1.6	169
489	AlGaN-based deep UV LEDs grown on sputtered and high temperature annealed AlN/sapphire. *Applied Physics Letters*, **2018**, 112, 041110	3.4	136
488	Optical polarization characteristics of ultraviolet (In)(Al)GaN multiple quantum well light emitting diodes. *Applied Physics Letters*, **2010**, 97, 171105	3.4	127
487	Selective growth of GaAs in the MOMBE and MOCVD systems. *Journal of Crystal Growth*, **1986**, 77, 303-308	1.6	125
486	The 2020 UV emitter roadmap. *Journal Physics D: Applied Physics*, **2020**, 53, 503001	3	123
485	Indium incorporation and emission wavelength of polar, nonpolar and semipolar InGaN quantum wells. *Semiconductor Science and Technology*, **2012**, 27, 024014	1.8	113
484	Performance Characteristics of UV-C AlGaN-Based Lasers Grown on Sapphire and Bulk AlN Substrates. *IEEE Photonics Technology Letters*, **2014**, 26, 342-345	2.2	92
483	Pulse repetition rate up to 92 GHz or pulse duration shorter than 110 fs from a mode-locked semiconductor disk laser. *Applied Physics Letters*, **2011**, 98, 071103	3.4	90
482	Efficient charge carrier injection into sub-250 nm AlGaN multiple quantum well light emitting diodes. *Applied Physics Letters*, **2014**, 105, 051113	3.4	83
481	High quality AlGaN grown on ELO AlN/sapphire templates. *Journal of Crystal Growth*, **2013**, 377, 32-36	1.6	83
480	Intentional □type doping by carbon in metalorganic MBE of GaAs. *Journal of Electronic Materials*, **1986**, 15, 57-59	1.9	75
479	Highly conductive n-AlxGa1□N layers with aluminum mole fractions above 80%. *Applied Physics Letters*, **2013**, 103, 212109	3.4	72

478	Effect of the AlN nucleation layer growth on AlN material quality. *Journal of Crystal Growth*, **2008**, 310, 4932-4934	1.6	68
477	High gain ultraviolet photodetectors based on AlGaN/GaN heterostructures for optical switching. *Applied Physics Letters*, **2011**, 98, 211114	3.4	66
476	12 W continuous-wave diode lasers at 1120 nm with InGaAs quantum wells. *Applied Physics Letters*, **2001**, 79, 1965-1967	3.4	65
475	Strongly transverse-electric-polarized emission from deep ultraviolet AlGaN quantum well light emitting diodes. *Applied Physics Letters*, **2015**, 107, 142101	3.4	63
474	Passively mode-locked Yb:KLu(WO4)2 oscillators. *Optics Express*, **2005**, 13, 3465-70	3.3	62
473	Structural and optical properties of nonpolar GaN thin films. *Applied Physics Letters*, **2008**, 92, 171904	3.4	56
472	Enhancement of light extraction in ultraviolet light-emitting diodes using nanopixel contact design with Al reflector. *Applied Physics Letters*, **2010**, 96, 081109	3.4	54
471	Growth of AlGaN and AlN on patterned AlN/sapphire templates. *Journal of Crystal Growth*, **2011**, 315, 200-203	1.6	54
470	High-power 808 nm lasers with a super-large optical cavity. *Semiconductor Science and Technology*, **2005**, 20, 621-624	1.8	54
469	Gaseous dopant sources in MOMBE/CBE. *Journal of Crystal Growth*, **1990**, 105, 383-392	1.6	54
468	Effective Thermal Management in Ultraviolet Light-Emitting Diodes With Micro-LED Arrays. *IEEE Transactions on Electron Devices*, **2013**, 60, 782-786	2.9	53
467	Composition of selectively grown InxGa1□As structures from locally resolved Raman spectroscopy. *Journal of Crystal Growth*, **1991**, 107, 151-155	1.6	53
466	Reactor and growth process optimization for growth of thick GaN layers on sapphire substrates by HVPE. *Journal of Crystal Growth*, **2005**, 277, 6-12	1.6	50
465	Carbon incorporation in MOMBE-grown Ga0.47In0.53As. *Journal of Crystal Growth*, **1989**, 95, 154-157	1.6	50
464	Correlation of InGaP(001) surface structure during growth and bulk ordering. *Physical Review B*, **1999**, 60, 8185-8190	3.3	48
463	Defect analysis in AlGaN layers on AlN templates obtained by epitaxial lateral overgrowth. *Journal of Crystal Growth*, **2014**, 402, 222-229	1.6	47
462	Quantitative analysis of in situ wafer bowing measurements for III-nitride growth on sapphire. *Journal of Crystal Growth*, **2008**, 310, 2432-2438	1.6	47
461	Real-time monitoring of MOVPE device growth by reflectance anisotropy spectroscopy and related optical techniques. *Journal of Crystal Growth*, **1998**, 195, 151-162	1.6	46

460	MOVPE growth of highly strained InGaAs/GaAs quantum wells. *Journal of Crystal Growth*, **1998**, 183, 511-518	1.6	46
459	High-power tensile-strained GaAsP-AlGaAs quantum-well lasers emitting between 715 and 790 nm. *IEEE Journal of Selected Topics in Quantum Electronics*, **1999**, 5, 780-784	3.8	44
458	. *IEEE Photonics Technology Letters*, **2012**, 24, 1603-1605	2.2	43
457	Effect of the barrier composition on the polarization fields in near UV InGaN light emitting diodes. *Applied Physics Letters*, **2008**, 92, 191912	3.4	43
456	High-temperature growth of AlN in a production scale 11 □2? MOVPE reactor. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2008**, 5, 1799-1801		43
455	Mode-locked InGaAs-AlGaAs disk laser generating sub-200-fs pulses, pulse picking and amplification by a tapered diode amplifier. *Optics Express*, **2009**, 17, 10820-34	3.3	42
454	Reliability issues of GaN based high voltage power devices. *Microelectronics Reliability*, **2011**, 51, 1710-17	1.6	41
453	Impact of band structure and transition matrix elements on polarization properties of the photoluminescence of semipolar and nonpolar InGaN quantum wells. *Physica Status Solidi (B): Basic Research*, **2011**, 248, 638-646	1.3	41
452	Semipolar GaN grown on m-plane sapphire using MOVPE. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2008**, 5, 1815-1817		41
451	Optical in-well pumping of a semiconductor disk laser with high optical efficiency. *IEEE Journal of Quantum Electronics*, **2005**, 41, 1439-1449	2	40
450	Low absorption loss p-AlGaN superlattice cladding layer for current-injection deep ultraviolet laser diodes. *Applied Physics Letters*, **2016**, 108, 151108	3.4	39
449	High-power UV-B LEDs with long lifetime **2015**,		38
448	Determination of band offsets in strained InxGa1□xAs□GaAs quantum wells by capacitance-voltage profiling and Schr□dinger-Poisson self-consistent simulation. *Physical Review B*, **2004**, 70,	3.3	38
447	Electrical properties and microstructure of vanadium-based contacts on ICP plasma etched n-type AlGaN:Si and GaN:Si surfaces. *Semiconductor Science and Technology*, **2013**, 28, 125015	1.8	37
446	Orientation control of GaN {112□2} and {101□3□} grown on (101□0) sapphire by metal-organic vapor phase epitaxy. *Journal of Crystal Growth*, **2010**, 312, 2171-2174	1.6	37
445	Proton and Heavy Ion Irradiation Effects on AlGaN/GaN HFET Devices. *IEEE Transactions on Nuclear Science*, **2006**, 53, 3661-3666	1.7	37
444	Doping of GaAs in metalorganic MBE using gaseous sources. *Journal of Crystal Growth*, **1987**, 81, 270-275	1.6	37
443	Passively mode-locked Yb:LuVO(4) oscillator. *Optics Express*, **2006**, 14, 11668-71	3.3	36

442	Degradation effects of the active region in UV-C light-emitting diodes. *Journal of Applied Physics*, **2018**, 123, 104502	2.5	35
441	Degradation of (InAlGa)N-based UV-B light emitting diodes stressed by current and temperature. *Journal of Applied Physics*, **2015**, 118, 094504	2.5	35
440	(Al,Ga)N overgrowth over AlN ridges oriented in [1120] and [1100] direction. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 2022-2024		34
439	Growth optimization during III-nitride multiwafer MOVPE using real-time curvature, reflectance and true temperature measurements. *Journal of Crystal Growth*, **2007**, 298, 202-206	1.6	34
438	High-power 810-nm GaAsP-AlGaAs diode lasers with narrow beam divergence. *IEEE Journal of Selected Topics in Quantum Electronics*, **2001**, 7, 334-339	3.8	34
437	Carbon in III-V Compounds: A Theoretical Approach. *Japanese Journal of Applied Physics*, **1992**, 31, 2483-2487	1.4	34
436	MOVPE-grown AlGaN-based tunnel heterojunctions enabling fully transparent UVC LEDs. *Photonics Research*, **2019**, 7, B7	6	34
435	Metamorphic Al 0.5 Ga 0.5 N:Si on AlN/sapphire for the growth of UVB LEDs. *Journal of Crystal Growth*, **2017**, 464, 185-189	1.6	33
434	Heat transfer and mass transport in a multiwafer MOVPE reactor: modelling and experimental studies. *Journal of Crystal Growth*, **1997**, 170, 66-71	1.6	33
433	290-fs pulses from a semiconductor disk laser. *Optics Express*, **2008**, 16, 5770-5	3.3	33
432	Passively cooled 940 nm laser bars with 73% wall-plug efficiency at 70 W and 25°C. *Electronics Letters*, **2005**, 41, 250	1.1	33
431	Gas Sensing of Nitrogen Oxide Utilizing Spectrally Pure Deep UV LEDs. *IEEE Journal of Selected Topics in Quantum Electronics*, **2017**, 23, 29-36	3.8	32
430	Temperature and excitation power dependent photoluminescence intensity of GaInN quantum wells with varying charge carrier wave function overlap. *Journal of Applied Physics*, **2010**, 107, 033510	2.5	32
429	A-plane GaN epitaxial lateral overgrowth structures: Growth domains, morphological defects, and impurity incorporation directly imaged by cathodoluminescence microscopy. *Applied Physics Letters* , **2008**, 92, 212111	3.4	32
428	Controlled coalescence of MOVPE grown AlN during lateral overgrowth. *Journal of Crystal Growth*, **2013**, 368, 83-86	1.6	31
427	Effect of temperature and strain on the optical polarization of (In)(Al)GaN ultraviolet light emitting diodes. *Applied Physics Letters*, **2011**, 99, 261105	3.4	31
426	High-power red laser diodes grown by MOVPE. *Journal of Crystal Growth*, **2007**, 298, 667-671	1.6	31
425	AlN growth on nano-patterned sapphire: A route for cost efficient pseudo substrates for deep UV LEDs. *Physica Status Solidi (A) Applications and Materials Science*, **2016**, 213, 3178-3185	1.6	31

424	Mechanisms of Implantation Damage Formation in AlxGa1−xN Compounds. *Journal of Physical Chemistry C*, **2016**, 120, 7277-7283	3.8	30
423	Degradation of (In)AlGaN-Based UVB LEDs and Migration of Hydrogen. *IEEE Photonics Technology Letters*, **2019**, 31, 529-532	2.2	29
422	1.9 W continuous-wave single transverse mode emission from 1060 nm edge-emitting lasers with vertically extended lasing area. *Applied Physics Letters*, **2014**, 105, 151105	3.4	29
421	Topography of (202−1) AlGaN, GaN and InGaN layers grown by metal-organic vapor phase epitaxy. *Journal of Crystal Growth*, **2012**, 356, 70-74	1.6	29
420	Correlation of sapphire off-cut and reduction of defect density in MOVPE grown AlN. *Physica Status Solidi (B): Basic Research*, **2016**, 253, 809-813	1.3	29
419	Spectroscopic process sensors in MOVPE device production. *Applied Physics A: Materials Science and Processing*, **1999**, 68, 309-313	2.6	28
418	Si Doping of GaN in Hydride Vapor-Phase Epitaxy. *Journal of Electronic Materials*, **2013**, 42, 820-825	1.9	27
417	Surface morphology of homoepitaxial GaN grown on non- and semipolar GaN substrates. *Physica Status Solidi (B): Basic Research*, **2011**, 248, 574-577	1.3	27
416	Design and realization of high-power DFB lasers **2004**,		27
415	Substituted arsines as As sources in MOMBE. *Journal of Crystal Growth*, **1990**, 105, 271-274	1.6	27
414	Current-induced degradation and lifetime prediction of 310 nm ultraviolet light-emitting diodes. *Photonics Research*, **2019**, 7, B36	6	27
413	GaN boules grown by high rate HVPE. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 1450-1454		26
412	Uniformity of the wafer surface temperature during MOVPE growth of GaN-based laser diode structures on GaN and sapphire substrate. *Journal of Crystal Growth*, **2011**, 315, 5-9	1.6	26
411	Real-time calibration of wafer temperature, growth rate and composition by optical in-situ techniques during AlxGa1−xAs growth in MOVPE. *Journal of Crystal Growth*, **2002**, 240, 87-97	1.6	26
410	Growth of strained GaAsSb layers on GaAs (001) by MOVPE. *Journal of Crystal Growth*, **2005**, 276, 347-353	2.6	26
409	Improved performance of UVC-LEDs by combination of high-temperature annealing and epitaxially laterally overgrown AlN/sapphire. *Photonics Research*, **2020**, 8, 589	6	26
408	The effects of magnesium doping on the modal loss in AlGaN-based deep UV lasers. *Applied Physics Letters*, **2017**, 110, 081103	3.4	25
407	Impact of AlN nucleation layer on strain in GaN grown on 4H-SiC substrates. *Journal of Crystal Growth*, **2013**, 371, 45-49	1.6	25

406	On the optical polarization properties of semipolar InGaN quantum wells. *Applied Physics Letters*, **2011**, 99, 051103	3.4	25
405	MOVPE process development for 650 nm VCSELS using optical in-situ techniques. *Journal of Crystal Growth*, **2002**, 235, 25-34	1.6	25
404	Semi-polar -GaN templates grown on 100 mm trench-patterned r-plane sapphire. *Physica Status Solidi (B): Basic Research*, **2015**, 252, 1189-1194	1.3	24
403	Solar-blind AlGaN MSM photodetectors with 24% external quantum efficiency at 0 V. *Electronics Letters*, **2015**, 51, 1598-1600	1.1	24
402	Impact of intermediate high temperature annealing on the properties of AlN/sapphire templates grown by metalorganic vapor phase epitaxy. *Japanese Journal of Applied Physics*, **2019**, 58, SC1002	1.4	23
401	Stabilization of sputtered AlN/sapphire templates during high temperature annealing. *Journal of Crystal Growth*, **2019**, 512, 142-146	1.6	23
400	**2013**,		23
399	Impact of electron irradiation on electron holographic potentiometry. *Applied Physics Letters*, **2014**, 105, 094102	3.4	23
398	Ultrahigh-brightness 850 nm GaAs/AlGaAs photonic crystal laser diodes. *Applied Physics Letters*, **2008**, 93, 221102	3.4	23
397	2MeV ion irradiation effects on AlGaN/GaN HFET devices. *Solid-State Electronics*, **2008**, 52, 1011-1017	1.7	23
396	In situ study of GaAs growth mechanisms using tri-methyl gallium and tri-ethyl gallium precursors in metal-organic vapour phase epitaxy. *Journal of Crystal Growth*, **2004**, 262, 78-83	1.6	23
395	High-power highly strained InGaAs quantum-well lasers operating at 1.2 □m. *IEEE Photonics Technology Letters*, **2002**, 14, 887-889	2.2	23
394	Red luminescence from freestanding GaN grown on LiAlO2 substrate by hydride vapor phase epitaxy. *Physica Status Solidi (A) Applications and Materials Science*, **2007**, 204, 846-849	1.6	22
393	High-power high-efficiency 1150-nm quantum-well laser. *IEEE Journal of Selected Topics in Quantum Electronics*, **2005**, 11, 1217-1222	3.8	22
392	Blue 489-nm picosecond pulses generated by intracavity frequency doubling in a passively mode-locked optically pumped semiconductor disk laser. *Applied Physics B: Lasers and Optics*, **2005**, 81, 443-446	1.9	22
391	Simple method for examining sulphur passivation of facets in InGaAs□AlGaAs (□0.98 □m) laser diodes. *Applied Physics Letters*, **1996**, 68, 2467-2468	3.4	22
390	AlGaN layer structures for deep UV emitters on laterally overgrown AlN/sapphire templates. *Physica Status Solidi (A) Applications and Materials Science*, **2013**, 210, 451-454	1.6	21
389	Growth parameter optimization of the GaInP/AlGaInP active zone of 635nm red laser diodes. *Journal of Crystal Growth*, **2008**, 310, 5175-5177	1.6	21

388	High-power highly reliable Al-free 940-nm diode lasers. *IEEE Journal of Selected Topics in Quantum Electronics*, **2001**, 7, 143-148	3.8	21
387	Measurement and simulation of top- and bottom-illuminated solar-blind AlGaN metal-semiconductor-metal photodetectors with high external quantum efficiencies. *Journal of Applied Physics*, **2015**, 118, 244504	2.5	20
386	Spatial clustering of defect luminescence centers in Si-doped low resistivity Al0.82Ga0.18N. *Applied Physics Letters*, **2015**, 107, 072103	3.4	20
385	Analysis of doping induced wafer bow during GaN:Si growth on sapphire. *Journal of Applied Physics*, **2012**, 112, 033503	2.5	20
384	. *IEEE Journal of Quantum Electronics*, **2011**, 47, 1014-1027	2	20
383	Laser Scribing for Facet Fabrication of InGaN MQW Diode Lasers on Sapphire Substrates. *IEEE Photonics Technology Letters*, **2010**, 22, 416-418	2.2	20
382	Hydride vapor phase epitaxy of GaN boules using high growth rates. *Journal of Crystal Growth*, **2010** , 312, 2537-2541	1.6	20
381	MOVPE growth optimization for laser diodes with highly strained InGaAs MQWs. *Journal of Crystal Growth*, **2007**, 298, 652-657	1.6	20
380	Freestanding 2-in GaN layers using lateral overgrowth with HVPE. *Journal of Crystal Growth*, **2008**, 310, 911-915	1.6	20
379	Effect of growth conditions and strain compensation on indium incorporation for diode lasers emitting above 1050nm. *Journal of Crystal Growth*, **2000**, 221, 496-502	1.6	20
378	Fe-doping in hydride vapor-phase epitaxy for semi-insulating gallium nitride. *Journal of Crystal Growth*, **2016**, 456, 97-100	1.6	20
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376	Investigation of inversion domain formation in AlN grown on sapphire by MOVPE. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2012**, 9, 496-498		19
375	Device Breakdown and Dynamic effects in GaN Power Switching Devices: Dependencies on Material Properties and Device Design. *ECS Transactions*, **2013**, 50, 211-222	1	19
374	Indium incorporation efficiency and critical layer thickness of (202□1) InGaN layers on GaN. *Applied Physics Letters*, **2012**, 101, 202102	3.4	19
373	(In)AlGaN deep ultraviolet light emitting diodes with optimized quantum well width. *Physica Status Solidi (A) Applications and Materials Science*, **2010**, 207, 2198-2200	1.6	19
372	Ultrashort pulse Yb:LaSc(3)(BO(3))(4) mode-locked oscillator. *Optics Express*, **2007**, 15, 15539-44	3.3	19
371	Freestanding two inch c-plane GaN layers grown on (100) □lithium aluminium oxide by hydride vapour phase epitaxy. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2006**, 3, 1439-1443		19

370	High-power 783 nm distributed-feedback laser. *Electronics Letters*, **2004**, 40, 123	1.1	19
369	Modeling and experimental verification of transport and deposition behavior during MOVPE of Ga1-xInxP in the Planetary Reactor. *Journal of Crystal Growth*, **2000**, 208, 85-92	1.6	19
368	Displacement Talbot lithography for nano-engineering of III-nitride materials. *Microsystems and Nanoengineering*, **2019**, 5, 52	7.7	19
367	UV-C Lasing From AlGaN Multiple Quantum Wells on Different Types of AlN/Sapphire Templates. *IEEE Photonics Technology Letters*, **2015**, 27, 1969-1972	2.2	18
366	Status and Prospects of AlN Templates on Sapphire for Ultraviolet Light-Emitting Diodes. *Physica Status Solidi (A) Applications and Materials Science*, **2020**, 217, 1901022	1.6	18
365	Comparative study of buffer designs for high breakdown voltage AlGaNGaN HFETs. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 2427-2429		18
364	Compositional dependence of the bowing parameter for highly strained InGaAs/GaAs quantum wells. *Physical Review B*, **2009**, 80,	3.3	18
363	High-Brightness and Ultranarrow-Beam 850-nm GaAs/AlGaAs Photonic Band Crystal Lasers and Single-Mode Arrays. *IEEE Journal of Selected Topics in Quantum Electronics*, **2009**, 15, 901-908	3.8	18
362	650-nm vertical-cavity surface-emitting lasers: laser properties and reliability investigations. *IEEE Photonics Technology Letters*, **2002**, 14, 1385-1387	2.2	18
361	Arsenic passivation of MOMBE grown GaAs surfaces. *Surface Science*, **1988**, 204, 485-490	1.8	18
360	Efficient carrier-injection and electron-confinement in UV-B light-emitting diodes. *Physica Status Solidi (A) Applications and Materials Science*, **2016**, 213, 210-214	1.6	18
359	V-pit to truncated pyramid transition in AlGaN-based heterostructures. *Semiconductor Science and Technology*, **2015**, 30, 114010	1.8	17
358	Growth of GaN boules via vertical HVPE. *Journal of Crystal Growth*, **2012**, 350, 89-92	1.6	17
357	Polarization of eigenmodes in laser diode waveguides on semipolar and nonpolar GaN. *Physica Status Solidi - Rapid Research Letters*, **2010**, 4, 1-3	2.5	17
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355	Study of damage formation and annealing of implanted III-nitride semiconductors for optoelectronic devices. *Nuclear Instruments & Methods in Physics Research B*, **2016**, 379, 251-254	1.2	16
354	Stress evolution during AlxGa1⊠N/AlN growth on sapphire. *Journal of Crystal Growth*, **2013**, 376, 54-58	1.6	16
353	AlGaN photodetectors for the UV-C spectral region on planar and epitaxial laterally overgrown AlN/sapphire templates. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2013**, 10, 294-297		16

352	InGaN□GaN Disk Laser for Blue-Violet Emission Wavelengths. *IEEE Photonics Technology Letters*, **2010**, 22, 652-654	2.2	16
351	Facet formation for laser diodes on nonpolar and semipolar GaN. *Physica Status Solidi (A) Applications and Materials Science*, **2010**, 207, 1361-1364	1.6	16
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349	High efficiency AlGaInP-based 650 nm vertical-cavity surface-emitting lasers. *Electronics Letters*, **2001**, 37, 1222	1.1	16
348	MOMBE of InAs on GaAs. *Journal of Crystal Growth*, **1990**, 105, 178-184	1.6	16
347	Defects in GaAs films grown by MOMBE. *Journal of Crystal Growth*, **1987**, 81, 281-287	1.6	16
346	Localization of current-induced degradation effects in (InAlGa)N-based UV-B LEDs. *Journal of Applied Physics*, **2018**, 124, 084504	2.5	16
345	Reliability of UVC LEDs fabricated on AlN/sapphire templates with different threading dislocation densities. *Applied Physics Letters*, **2020**, 117, 241104	3.4	15
344	Effect of Electron Blocking Layer Doping and Composition on the Performance of 310 nm Light Emitting Diodes. *Materials*, **2017**, 10,	3.5	15
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342	Impact of light polarization on photoluminescence intensity and quantum efficiency in AlGaN and AlInGaN layers. *Applied Physics Letters*, **2012**, 101, 242102	3.4	15
341	Anisotropic strain on phonons in a-plane GaN layers studied by Raman scattering. *Journal of Materials Science: Materials in Electronics*, **2008**, 19, 51-57	2.1	15
340	Feedback controlled growth of strain-balanced InGaAs multiple quantum wells in metal-organic vapour phase epitaxy using anin situcurvature sensor. *Semiconductor Science and Technology*, **2006**, 21, L45-L48	1.8	15
339	Optimization of MOVPE growth for 650nm-emitting VCSELs. *Journal of Crystal Growth*, **2000**, 221, 663-667	2.6	15
338	Optimization of GaAsP/AlGaAs-based QW laser structures for high power 800 nm operation. *Journal of Electronic Materials*, **2000**, 29, 53-56	1.9	15
337	Carbon doped GaAs grown in low pressure-metalorganic vapor phase epitaxy using carbon tetrabromide. *Journal of Electronic Materials*, **1995**, 24, 1719-1722	1.9	15
336	MOVPE growth of AlxGa1-xN with x ~ 0.5 on epitaxial laterally overgrown AlN/sapphire templates for UV-LEDs. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2014**, 11, 377-380		14
335	Analysis of crystal orientation in AlN layers grown on m-plane sapphire. *Journal of Crystal Growth*, **2014**, 400, 54-60	1.6	14

334	Excitonic recombination in epitaxial lateral overgrown AlN on sapphire. *Applied Physics Letters*, **2013**, 103, 212108	3.4	14
333	HVPE of Al Ga1 N layers on planar and trench patterned sapphire. *Journal of Crystal Growth*, **2012**, 353, 129-133	1.6	14
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331	5.6-W Broad-Area Lasers With a Vertical Far-Field Angle of 31^{circ} Emitting at 670 nm. *IEEE Photonics Technology Letters*, **2008**, 20, 575-577	2.2	14
330	Exciton resonance tuning for the generation of subpicosecond pulses from a mode-locked semiconductor disk laser. *Applied Physics Letters*, **2006**, 89, 141107	3.4	14
329	3-W Broad Area Lasers and 12-W Bars With Conversion Efficiencies up to 40% at 650 nm. *IEEE Journal of Selected Topics in Quantum Electronics*, **2007**, 13, 1188-1193	3.8	14
328	Highly strained very high-power laser diodes with InGaAs QWs. *Journal of Crystal Growth*, **2003**, 248, 354-358	1.6	14
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325	Residual donor contamination in MOCVD, MOMBE and MBE GaAs studied by far-infrared spectroscopy. *Semiconductor Science and Technology*, **1989**, 4, 782-790	1.8	14
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323	Effect of the GaN:Mg Contact Layer on the Light-Output and Current-Voltage Characteristic of UVB LEDs. *Physica Status Solidi (A) Applications and Materials Science*, **2018**, 215, 1700643	1.6	13
322	Degradation behavior of AlGaN-based 233 nm deep-ultraviolet light emitting diodes. *Semiconductor Science and Technology*, **2018**, 33, 095017	1.8	13
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